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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/713,198	11/17/2003	Seung Hee Nam	8733.936.00-US	9565
30827	7590	11/02/2006	EXAMINER	
MCKENNA LONG & ALDRIDGE LLP 1900 K STREET, NW WASHINGTON, DC 20006			QI, ZHI QIANG	
			ART UNIT	PAPER NUMBER
			2871	

DATE MAILED: 11/02/2006

Please find below and/or attached an Office communication concerning this application or proceeding.

<b>Office Action Summary</b>	<b>Application No.</b>	<b>Applicant(s)</b>	
	10/713,198	NAM ET AL.	
	<b>Examiner</b>	<b>Art Unit</b>	
	Mike Qi	2871	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --  
**Period for Reply**

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

**Status**

1) Responsive to communication(s) filed on 22 September 2006.  
 2a) This action is **FINAL**.                                    2b) This action is non-final.  
 3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

**Disposition of Claims**

4) Claim(s) 1-3,5 and 6 is/are pending in the application.  
 4a) Of the above claim(s) \_\_\_\_\_ is/are withdrawn from consideration.  
 5) Claim(s) \_\_\_\_\_ is/are allowed.  
 6) Claim(s) 1-3,5 and 6 is/are rejected.  
 7) Claim(s) \_\_\_\_\_ is/are objected to.  
 8) Claim(s) \_\_\_\_\_ are subject to restriction and/or election requirement.

**Application Papers**

9) The specification is objected to by the Examiner.  
 10) The drawing(s) filed on \_\_\_\_\_ is/are: a) accepted or b) objected to by the Examiner.  
 Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).  
 Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).  
 11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

**Priority under 35 U.S.C. § 119**

12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).  
 a) All    b) Some \* c) None of:  
 1. Certified copies of the priority documents have been received.  
 2. Certified copies of the priority documents have been received in Application No. \_\_\_\_\_.  
 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

\* See the attached detailed Office action for a list of the certified copies not received.

**Attachment(s)**

1) Notice of References Cited (PTO-892)  
 2) Notice of Draftsperson's Patent Drawing Review (PTO-948)  
 3) Information Disclosure Statement(s) (PTO/SB/08)  
 Paper No(s)/Mail Date \_\_\_\_\_.  
 4) Interview Summary (PTO-413)  
 Paper No(s)/Mail Date. \_\_\_\_\_.  
 5) Notice of Informal Patent Application  
 6) Other: \_\_\_\_\_.

## DETAILED ACTION

### ***Claim Objections***

1. Claims 5 and 6 are objected to because of the following informalities: claim 4 has been canceled, so that the claims 5 and 6 cannot be dependent on the claim 4, and it seems to be dependent on claim 1. Appropriate correction is required.

### ***Claim Rejections - 35 USC § 103***

2. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

3. Claims 1, 2 and 5-6 are rejected under 35 U.S.C. 103(a) as being unpatentable over US 6,380,559 B1 (Park et al) in view of US 6,429,057 B1 (Hong et al).

Regarding claim 1, Park teaches (col.6, line 51 – col.13, line 52; Figs.1-5) that a fabrication method of a liquid crystal display panel comprising forming a substrate including a plurality of thin film transistor array, the thin film transistor array having a thin film transistor (TFT 3) at crossings of gate lines (22) and data lines (62) formed on a substrate, a gate pad part including a gate pad (24) connected to the gate line (22) and a data pad part including a data pad (64) connected to the data line (62), wherein the step of forming the thin film transistor array substrate comprises the step of:

- forming gate line assembly (gate pattern) including gate electrode of the thin film transistor, gate line (22) connected to the gate electrode and the gate

pad (24) connected to the gate line (22) (see Fig.2) on the substrate by using mask (see col.2, lines 55-64) that would be by use of a first masking process;

- forming a gate insulation film (30) on the substrate (10) where the gate pattern is formed (see Fig.4);
- forming data line assembly (source/drain pattern) including a source electrode (65) and a drain electrode (66) of the thin film transistor, a data line (62) connected to the source electrode, a data pad (64) connected to the data line (62), a source/drain pattern including a storage capacitors (such as pixel electrode 82 overlapped with gate line 22 as shown in Fig.5), and a semiconductor pattern is formed by etching the passivation layer (see col.2, line 59 – col.3, line13), i.e., a semiconductor pattern formed in the lower part according to the source/drain pattern on the gate insulating film and such forming process by using second mask that would be by use of a second masking process;
- forming pixel electrode (using ITO transparent conductive electrode) by using mask (see col.3, lines 14-17), and the pixel electrode (82) is connected to the drain electrode (66), and the pixel electrode can be a storage electrode, and such transparent electrode (pixel electrode) pattern including a data pad protection electrode (such as double layered structure 642, 641 for the data pad 64), and such process is formed by mask, and that is by a third masking process;
- forming a passivation layer using a mask on the substrate.

Park does not explicitly teach arranging a cutting-off plate on a remainder region of the substrate other than the region of the pad part (display area), and exposing the gate pad of the pad part and the data pad protection electrode (peripheral area) by a etching process using the cutting-off plate, and this application as claimed differs with Park is the step of forming a protection film on the substrate after the transparent electrode pattern forming process.

Park further teaches (col.10, line 26 –col.12, line 67; Figs.9-12) that the etching process using mask (such as mask 300 and 400).

The function of the cutting-off plate is the same as the function of a mask, because the cutting-off plate having open portion and opaque portion that allows the light passing though the open portion; and using mask to expose the gate pad of the pad part and the data pad electrode by etching process using a mask, and arranging a mask on a region to form the pad part, so that the opaque portion on a region of the substrate other than the region of the pad part. Park further teaches (col.10, lines 28-45) that the light exposure at the display area D is different from the light exposure at the peripheral area P, such that the molecules at the display area and at the peripheral area being resolved by using mask to a predetermined depth from the surface.

Therefore, it would have been obvious to those skilled in the art at the time the invention was made to modify the fabrication method of a liquid crystal display panel of Park with the teachings of arranging a mask (cutting-off plate) and exposing the gate pad and the data pad protection electrode by etching process using the mask (cutting-off plate) as taught by Park, since the skilled in the art would be motivated for obtaining

the molecules at the display area and at the peripheral area being resolved by using mask to a predetermined depth from the surface (col.10, lines 28-45).

Concerning the difference of the steps order wherein forming a protection film on the substrate after the transparent electrode pattern forming process, **Hong** further teaches (col.2, lines 5-23) that a method of manufacturing thin film transistor array in which forming a gate wire using first photolithography process, forming a data conductor layer using a second photolithography process, forming a conductive pattern (pixel electrode pattern) using a third photolithography process, and finally a passivation layer (a protection film) is formed by a fourth photolithography process, such that the step of forming entirely a protection film on the substrate after forming the transparent electrode (pixel electrode) pattern. **Hong** further teaches (col.1, lines 9-11) that such manufacturing method would reduce the number of manufacturing steps.

Therefore, it would have been obvious to those skilled in the art at the time the invention was made to modify the fabrication method of a liquid crystal display panel of **Park** with the teachings of forming a passivation layer after forming the pixel electrode pattern as taught by **Hong**, since the skilled in the art would be motivated for reducing the number manufacturing steps.

Regarding claim 2, **Park** teaches (col.1, lines 13-24) that generally, liquid crystal display is formed with two glass substrates (TFT array substrate and color filter substrate), and the forming method performing photolithography by using mask. Such that the gate pad and the data pad electrode are exposed, and that is a general manufacturing method, and that would have been at least obvious.

Regarding claims 5 and 6, Park teaches (col.3, lines 29-30) that the etching for forming the gate pad and data pad being performed by using dry etching.

4. Claim 3 is rejected under 35 U.S.C. 103(a) as being unpatentable over Park and Hong as applied to claims 1, 2 and 5-6 above, and further in view of US 6,255,130 B1 (Kim).

Regarding claim 3, Park and Hong teach the invention set forth above except for that the cutting-off plate is made of a metal.

Kim teaches (col.9, lines 49-63; Fig.7B) that a photomask (400) having a plurality of slits (410) (open portion), and a metal Cr layer is coated on the mask (400) to reduce the amount of exposing light.

Therefore, it would have been obvious to those skilled in the art at the time the invention was made to modify the fabrication method of a liquid crystal display panel of Park with the teachings of using a metal cutting-off plate as taught by Kim, since the skilled in the art would be motivated for achieving efficiently shield the light exposing in the opaque portion of the cutting-off plate (col.9, lines 60-64).

### ***Response to Arguments***

5. Applicant's arguments filed on September 22, 2006 have been fully considered but they are not persuasive.

In response to applicant's argument that the cited reference Park is different from this application wherein, in the claim 1, the step of forming a protection film after forming the transparent electrode (pixel electrode) pattern, it is respectfully pointed out that the

reference Hong teaches (col.2, lines 5-23) that a method of manufacturing thin film transistor array in which finally a passivation layer (a protection film) is formed by a fourth photolithography process, such that forming entirely a protection film on the substrate after forming the transparent electrode (pixel electrode) pattern. Hong further teaches (col.1, lines 9-11) that such manufacturing method would reduce the number of manufacturing steps, and that would render an obviousness.

***Conclusion***

6. Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

7. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Mike Qi whose telephone number is (571) 272-2299. The examiner can normally be reached on M-T 7:30 am-6:00 pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, David Nelms can be reached on (571) 272-1787. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

Mike Qi  
October 30, 2006

  
ANDREW SCHECHTER  
PRIMARY EXAMINER